

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S39	1586	(257/E27.061 or 257/E27.062 or 257/E27.064).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/01/04 18:00
S41	128	(257/E27.061 or 257/E27.062 or 257/E27.064).ccls. and @ad<"20030121" and ((gate with (oxide or insulat\$5 or dielectric)) same (halfnium or hf or zirconium or zr or titanium or ti or lanthanum or la or scandium or sc))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/01/04 18:07
S42	209	(257/E27.061 or 257/E27.062 or 257/E27.064).ccls. and @ad<"20030121" and ((gate with (oxide or insulat\$5 or dielectric)) same (yttrium or Y or lutetium or lu or lawrencium or lr or vanadium or v or niobium or nb or tantalum or ta or dubnium or db or cesium or ce or praseodymium or pr or neodymium or nd or promethium or pr or samarium or sm or gadolinium or terbium or gd or tb or dysprosium or dy or holmium or ho or erbium or er or thulium or tm or ytterbium or yb or iii or iv or v))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/01/04 18:39
S43	129	(257/E27.061 or 257/E27.062 or 257/E27.064).ccls. and @ad<"20030121" and ((gate with (oxide or insulat\$5 or dielectric)) same (halfnium or hf or zirconium or zr or titanium or ti or lanthanum or la or scandium or sc or rutherfordium or rf))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/01/04 18:39
S44	256	257/369.ccls. and @ad<"20030121" and (gate same ((oxide or insulat\$5 or dielectric) with (hafnium or hf or zirconium or zr or titanium or ti or lanthanum or la or scandium or sc or rutherfordium or rf or yttrium or Y or lutetium or lu or lawrencium or lr or aluminum or al)))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/01/04 18:45

S45	103	257/369.ccls. and @ad<"20030121" and (gate same ((oxide or insulat\$5 or dielectric) with (yttrium or Y or lutetium or lu or lawrencium or lr or vanadium or v or niobium or nb or tantalum or ta or dubnium or db or cesium or ce or praseodymium or pr or neodymium or nd or promethium or pr or samarium or sm or gadolinium or terbium or gd or tb or dysprosium or dy or holmium or ho or erbium or er or thulium or tm or ytterbium or yb)))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/01/04 18:48
S46	288	(257/405 or 257/411).ccls. and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (hafnium or hf or zirconium or zr or titanium or ti or lanthanum or la or scandium or sc or rutherfordium or rf or yttrium or Y or lutetium or lu or lawrencium or lr or aluminum or al)))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/01/04 18:50
S23	41	(257/405 or 257/411).ccls. and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (yttrium or Y or lutetium or lu or lawrencium or lr or vanadium or v or niobium or nb or tantalum or ta or dubnium or db or cesium or ce or praseodymium or pr or neodymium or nd or promethium or pr or samarium or sm or gadolinium or terbium or gd or tb or dysprosium or dy or holmium or ho or erbium or er or thulium or tm or ytterbium or yb or aluminum or al))) not S22	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/01/04 18:52
S47	289	(257/405 or 257/411).ccls. and @ad<"20030121" and (gate same ((oxide or insulat\$5 or dielectric) with (yttrium or Y or lutetium or lu or lawrencium or lr or vanadium or v or niobium or nb or tantalum or ta or dubnium or db or cesium or ce or praseodymium or pr or neodymium or nd or promethium or pr or samarium or sm or gadolinium or terbium or gd or tb or dysprosium or dy or holmium or ho or erbium or er or thulium or tm or ytterbium or yb or aluminum or al)))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/01/04 18:52

S48	41	(257/405 or 257/411).cccls. and @ad<"20030121" and (gate same ((oxide or insulat\$5 or dielectric) with (yttrium or Y or lutetium or lu or lawrencium or lr or vanadium or v or niobium or nb or tantalum or ta or dubnium or db or cesium or ce or praseodymium or pr or neodymium or nd or promethium or pr or samarium or sm or gadolinium or terbium or gd or tb or dysprosium or dy or holmium or ho or erbium or er or thulium or tm or ytterbium or yb or aluminum or al))) not S46	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/01/04 18:53
S49	39	(257/645 or 257/651).cccls. and @ad<"20030121" and (gate same ((oxide or insulat\$5 or dielectric) with (boron or B or aluminum or al or gallium or ga or indium or in or thallium or tl or ("iii" near3 (element or compound))))))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/01/04 18:53
S50	733	(c?mos or c?mis or c?mosfet or c?misfet or (complementary near3 (fet or mos or mis or mosfet or misfet or transistor)) or (p?mos and n?mos) or (p?mosfet and n?mosfet) or (p?fet and n?fet)) and @ad<"20030121" and (gate same ((oxide or insulat\$5 or dielectric) with (hafnium or hf or zirconium or zr or titanium or ti or ruthenium or ru or Sn or tin or Pb or lead or ("iv" near3 (metal or element or compound))))))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/01/04 18:58
S51	655	(cmos or cmosfet or cmis or cmisfet or c?mos or c?mis or c?mosfet or c?misfet or (complementary near3 (fet or mos or mis or mosfet or misfet or transistor)) or (p?mos and n?mos) or (p?mosfet and n?mosfet) or (p?fet and n?fet) or (pmos and nmos) or (pmosfet and nmosfet) or (pfet and nfet)) and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (hafnium or hf or zirconium or zr or titanium or ti or ruthenium or ru or Sn or tin or Pb or lead or ("iv" near3 (metal or element or compound)))))) same (boron or b or gallium or ga or indium or thallium or tl) not S50	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/01/04 19:02

S52	5465	(cmos or cmosfet or cmis or cmisfet or c?mos or c?mis or c?mosfet or c?misfet or (complementary near3 (fet or mos or mis or mosfet or misfet or transistor)) or (p?mos and n?mos) or (p?mosfet and n?mosfet) or (p?fet and n?fet) or (pmos and nmos) or (pmosfet and nmosfet) or (pfet and nfet)) and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (boron or b)))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/01/04 19:03
S54	823	(cmos or cmosfet or cmis or cmisfet or c?mos or c?mis or c?mosfet or c?misfet or (complementary near3 (fet or mos or mis or mosfet or misfet or transistor)) or (p?mos and n?mos) or (p?mosfet and n?mosfet) or (p?fet and n?fet) or (pmos and nmos) or (pmosfet and nmosfet) or (pfet and nfet)) and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (boron))) and (positive or negative)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/01/04 19:03
S53	1862	(cmos or cmosfet or cmis or cmisfet or c?mos or c?mis or c?mosfet or c?misfet or (complementary near3 (fet or mos or mis or mosfet or misfet or transistor)) or (p?mos and n?mos) or (p?mosfet and n?mosfet) or (p?fet and n?fet) or (pmos and nmos) or (pmosfet and nmosfet) or (pfet and nfet)) and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (boron or b))) and (positive or negative)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/01/04 19:04

S55	192	(cmos or cmosfet or cmis or cmisfet or c?mos or c?mis or c?mosfet or c?misfet or (complementary near3 (fet or mos or mis or mosfet or misfet or transistor)) or (p?mos and n?mos) or (p?mosfet and n?mosfet) or (p?fet and n?fet) or (pmos and nmos) or (pmosfet and nmosfet) or (pfet and nfet)) and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (boron or b))) and (((positive or negative) near4 charg\$4) with (dop\$4 or insulat\$4 or dielectric or oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/01/05 22:59
S56	115	(cmos or cmosfet or cmis or cmisfet or c?mos or c?mis or c?mosfet or c?misfet or (complementary near3 (fet or mos or mis or mosfet or misfet or transistor)) or (p?mos and n?mos) or (p?mosfet and n?mosfet) or (p?fet and n?fet) or (pmos and nmos) or (pmosfet and nmosfet) or (pfet and nfet)) and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (boron or boride))) and (((positive or negative) near4 charg\$4) with (dop\$4 or insulat\$4 or dielectric or oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/01/06 01:00
S58	2280	(cmos or cmosfet or cmis or cmisfet or c?mos or c?mis or c?mosfet or c?misfet or (complementary near3 (fet or mos or mis or mosfet or misfet or transistor)) or (p?mos and n?mos) or (p?mosfet and n?mosfet) or (p?fet and n?fet) or (pmos and nmos) or (pmosfet and nmosfet) or (pfet and nfet)) and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (boron))) not S56	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/01/06 01:02